



N-Channel 120 V (D-S) MOSFET

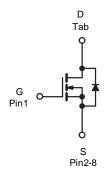
PRODUCT SUMMARY Q_g (Typ.) $V_{DS}(V)$ $R_{DS(on)}(m\Omega)(Typ.)$ I_D (A)^a 120 1.35 at $V_{GS} = 10 \text{ V}$ 393 135 nC

FEATURES

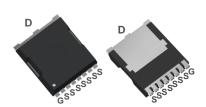
- DT-SGT Power MOSFET
- · Very Low On-resistance
- Excellent FOM(Figure of Merit)
- 100% ΔVDS & UIS & Rg Tested

APPLICATIONS

- DC-DC Converter
- · Hard Switching and High Speed Circuit
- Synchronous Rectification in SMPS



TOLL Pin Configuration



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)							
PARAMETER	SYMBOL	LIMIT	UNIT				
Drain-Source Voltage	V _{DS}	120	V				
Gate-Source Voltage	V_{GS}	± 20					
Continuous Dunin Courset /T 475 90\2	T _C = 25 °C	1	393	А			
Continuous Drain Current (T _J = 175 °C) ^a	T _C = 100 °C	l _D	278				
Pulsed Drain Current ^b	I _{DM}	1574					
Single Avalanche Energy	E _{AS}	2074	mJ				
Maximum Power Dissipation ^c	T _C = 25 °C	В	500	W			
waximum rower bissipation	T _C = 100 °C	$ P_D$	250	\ \v			
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	25	°C/W			
Junction-to-Case (Drain)	R _{thJC}	0.3	C/VV			

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0,JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL TEST CONDITIONS			TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	120	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.0	-	4.0	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA
Zoro Coto Voltogo Drain Current		V _{DS} = 120 V, V _{GS} = 0 V	-	-	1	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 96 V, V _{GS} = 0 V, T _J = 125 °C	-	-	100	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	393	-	-	Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V, I _D = 80 A	-	1.35	1.6	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = 5 V, I _D = 20 A	-	74	-	S
Dynamic ^b						
Input Capacitance	C _{iss}		-	10308	-	pF
Output Capacitance	Coss	V _{GS} = 0 V, V _{DS} = 60 V, f = 1 MHz	-	4393	-	
Reverse Transfer Capacitance	C _{rss}		-	41	-	
Total Gate Charge ^c	Qg		-	135	-	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 60 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 80 \text{ A}$	-	53	-	
Gate-Drain Charge ^c	Q_{gd}]	-	20	-	
Gate Resistance	R_g	f = 1 MHz	-	1.5	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	33	-	ns
Rise Time ^c	t _r	$V_{DD} = 60 \text{ V}, \text{ R}_{GEN} = 3 \Omega, \text{ I}_{D} = 80 \text{ A},$	-	42	=	
Turn-Off Delay Time ^c	t _{d(off)}	V _{GS} = 10 V	-	97	=	
Fall Time ^c	t _f]	-	43	-	
Drain-Source Body Diode Ratings and	Characterist	tics ^b (T _C = 25 °C)				
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	393	Α
Pulsed Current	I _{SM}		-	-	1574	Α
Forward Voltage ^a	V _{SD}	I _F = 2 A, V _{GS} = 0 V	-	0.7	1.2	V
Reverse Recovery Time	t _{rr}	1 00 A di/dt = 400 A/cc	-	110	-	ns
Reverse Recovery Charge	Q _{rr}	I _F = 80 A, di/dt = 100 A/μs	-	301	-	nC

Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (25°C unless otherwise noted)

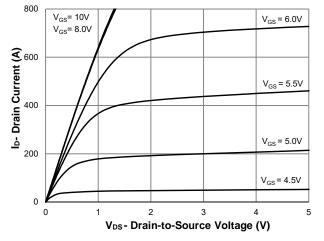


Figure 1: Output Characteristics

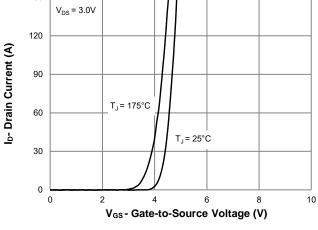


Figure 2: Transfer Characteristics

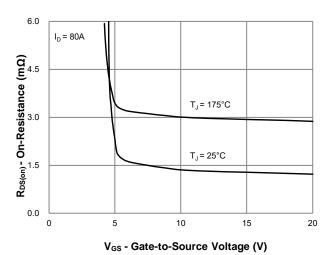


Figure 3: On-Resistance vs. Gate-Source Voltage

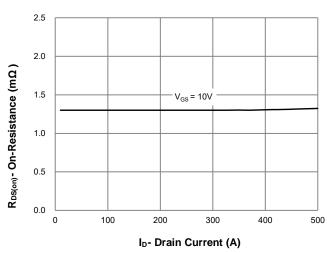


Figure 4: On-Resistance vs. Gate-Source Voltage

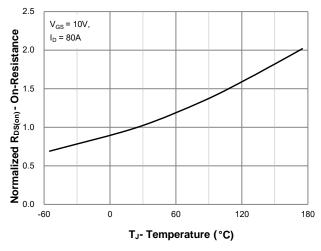


Figure 5: On-Resistance vs. Junction Temperature

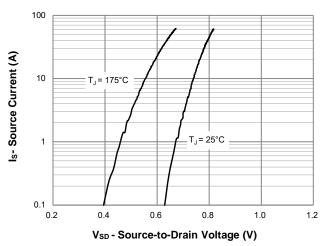


Figure 6: Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTICS (25°C unless otherwise noted)

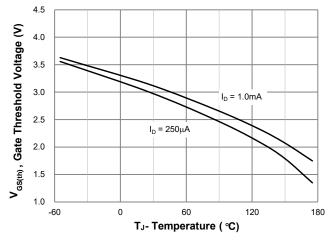


Figure 7: Gate Threshold Variation vs. Junction Temperature

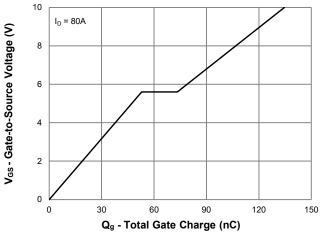
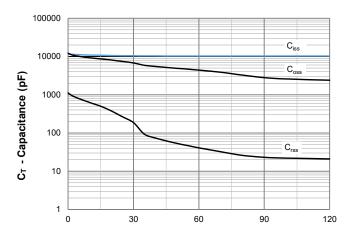
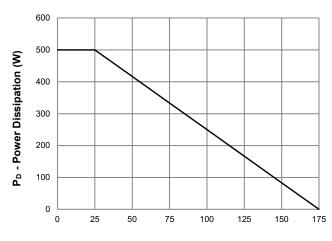


Figure 8: Gate Charge Characteristics



V_{DS} - Drain-to-Source Voltage (V)



T_C - Case Temperature (°C) Figure 10: Power Derating



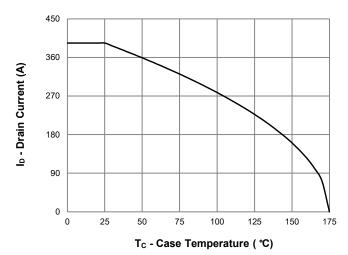
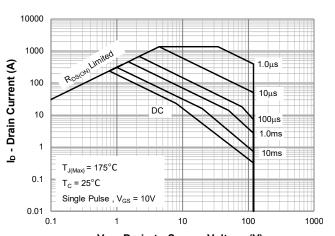


Figure 11: Current Derating



 V_{DS} - Drain-to-Source Voltage (V)

Figure 12: Safe Operating Area



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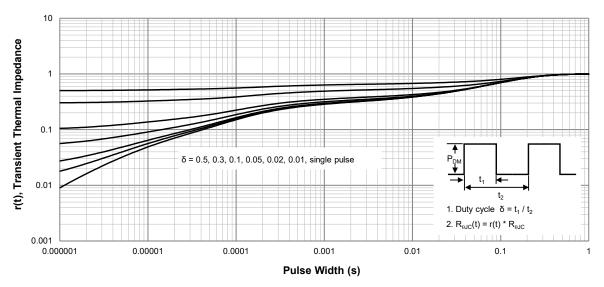
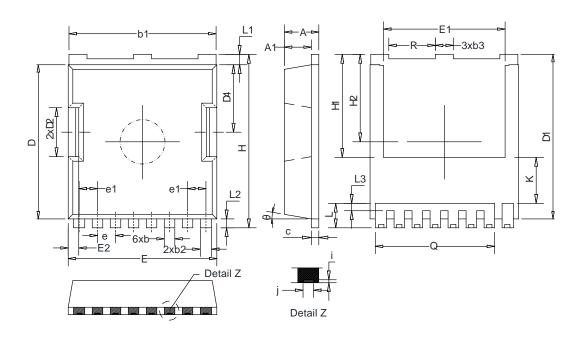


Figure 13: Normalized Maximum Transient Thermal Impedance



TOLL PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max	Symbol	Min	Тур	Max
А	2.05	2.30	2.65	E2	0.40	0.70	0.90
A1	1.50	1.80	210	Н	11.30	11.70	12.10
b	0.50	0.70	0.90	H1	6.95 BSC		
b1	9.50	9.80	1005	H2	5.90 BSC		
b2	0.50	0.75	1.00	i	0.10 REF		
b3	1.00	1.20	1.45	j	0.35 REF		
С	0.30	0.50	0.75	K	3.10 REF		
D	10.10	10.40	10.70	L	1.45	1.65	1.85
D1	10.80	11.10	11.40	L1	0.50	0.70	0.90
D2	3.10	3.30	3.50	L2	0.40	0.60	0.80
D4	4.35	4.55	4.80	L3	0.30	0.50	0.70
е	1.20 BSC			Q	7.95 REF		
e1	1.225 BSC		R	2.80	3.10	3.35	
Е	9.65	9.90	10.15	θ	10°REF		
E1	7.80	8.10	8.50				





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